## MC100EPT26

### 3.3 V 1:2 Fanout Differential LVPECL/LVDS to LVTTL Translator

## Description

The MC100EPT26 is a $1: 2$ Fanout Differential LVPECL/LVDS to LVTTL translator. Because LVPECL (Positive ECL) or LVDS levels are used only +3.3 V and ground are required. The small outline 8 -lead package and the 1:2 fanout design of the EPT26 makes it ideal for applications which require the low skew duplication of a signal in a tightly packed PC board.
The $\mathrm{V}_{\text {BB }}$ output allows the EPT26 to be used in a Single-Ended input mode. In this mode the $V_{\mathrm{BB}}$ output is tied to the $\overline{\mathrm{D} 0}$ input for a non-inverting buffer or the D0 input for an inverting buffer. If used, the $\mathrm{V}_{\mathrm{BB}}$ pin should be bypassed to ground with $>0.01 \mu \mathrm{~F}$ capacitor. For a Single-Ended direct connection, use an external voltage reference source such as a resistor divider. Do not use $\mathrm{V}_{\mathrm{BB}}$ for a Single-Ended direct connection or port to another device.

## Features

- 1.4 ns Typical Propagation Delay
- Maximum Frequency $=>275 \mathrm{MHz}$ Typical
- The 100 Series Contains Temperature Compensation
- Operating Range: $\mathrm{V}_{\mathrm{CC}}=3.0 \mathrm{~V}$ to 3.6 V with $\mathrm{GND}=0 \mathrm{~V}$
- 24 mA TTL outputs
- Q Outputs Will Default LOW with Inputs Open or at $\mathrm{V}_{\mathrm{EE}}$
- VBB Output
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant

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MARKING DIAGRAMS*

= Assembly Location
$Y \quad=$ Year
W = Work Week
M = Date Code
= Pb-Free Package
(Note: Microdot may be in either location)
*For additional marking information, refer to Application Note AND8002/D.

ORDERING INFORMATION

| Device | Package | Shipping $\dagger$ |
| :---: | :---: | :---: |
| MC100EPT26DG | SOIC-8 NB <br> (Pb-Free) | 98 Units/Tube |
| MC100EPT26DR2G | SOIC-8 NB <br> (Pb-Free) | 2500 Tape \& Reel |
| MC100EPT26DTG | TSSOP-88 <br> (Pb-Free) | 100 Tape \& Reel |
| MC100RPT26DTR2G | TSSOP-8 <br> (Pb-Free) | 2500 Tape \& Reel |
| MC100EPT26MNR4G | DFN8 <br> (Pb-Free) | 1000 Tape \& Reel |

$\dagger$ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## MC100EPT26



Table 1. PIN DESCRIPTION

| Pin | Function |
| :--- | :--- |
| Q0, Q1 | LVTTL Outputs |
| D0**, D1^* $^{2}$ | Differential LVPECL Inputs Pair |
| V $_{\text {CC }}$ | Positive Supply |
| VBB $^{\text {BR }}$ | Output Reference Voltage |
| GND | Ground |
| NC | No Connect |
| EP | (DFN8 only) Thermal exposed pad must be con- <br> nected to a sufficient thermal conduit. Electric- <br> ally connect to the most negative supply (GND) <br> or leave unconnected, floating open. |

** Pins will default to $\mathrm{V}_{\mathrm{CC}} / 2$ when left open.
Figure 1. 8-Lead Pinout and Logic Diagram

Table 2. ATTRIBUTES

| Characteristics | Value |
| :--- | :---: |
| Internal Input Pulldown Resistor | $50 \mathrm{k} \Omega$ |
| Internal Input Pullup Resistor | $50 \mathrm{k} \Omega$ |
| ESD Protection <br> Human Body Model <br> Machine Model <br> Charged Device Model | $>1.5 \mathrm{kV}$ <br> Moisture Sensitivity, Indefinite Time Out of Drypack (Note 1) <br> $>100 \mathrm{~V}$ <br> $>2 \mathrm{kV}$ |
| SOIC-8 NB | Pb-Free Pkg |
| TSSOP-8 |  |
| DFN8 | Level 1 |
| Flammability Rating | Level 3 |
| Transistor Count | Oxygen Index: 28 to 34 |
| Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test | UL 94 V-0 @ 0.125 in |

1. For additional information, see Application Note AND8003/D.

## MC100EPT26

Table 3. MAXIMUM RATINGS

| Symbol | Parameter | Condition 1 | Condition 2 | Rating | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{CC}}$ | Positive Power Supply | GND $=0 \mathrm{~V}$ |  | 3.8 | V |
| $\mathrm{V}_{\text {IN }}$ | Input Voltage | GND $=0 \mathrm{~V}$ | $\mathrm{V}_{1} \leq \mathrm{V}_{\mathrm{CC}}$ | 0 to 3.8 | V |
| $\mathrm{I}_{\mathrm{BB}}$ | $\mathrm{V}_{\text {BB }}$ Sink/Source |  |  | $\pm 0.5$ | mA |
| $\mathrm{T}_{\mathrm{A}}$ | Operating Temperature Range |  |  | -40 to +85 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\text {stg }}$ | Storage Temperature Range |  |  | -65 to +150 | ${ }^{\circ} \mathrm{C}$ |
| $\theta_{\text {JA }}$ | Thermal Resistance (Junction-to-Ambient) | $\begin{array}{\|l\|} \hline 0 \text { lfpm } \\ 500 \text { lfpm } \end{array}$ | $\begin{aligned} & \text { SOIC-8 NB } \\ & \text { SOIC-8 NB } \end{aligned}$ | $\begin{aligned} & \hline 190 \\ & 130 \end{aligned}$ | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| $\theta_{\mathrm{Jc}}$ | Thermal Resistance (Junction-to-Case) | Standard Board | SOIC-8 NB | 41 to 44 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| $\theta_{\text {JA }}$ | Thermal Resistance (Junction-to-Ambient) | $\begin{array}{\|l\|} \hline 0 \text { lfpm } \\ 500 \text { lfpm } \end{array}$ | $\begin{aligned} & \hline \text { TSSOP-8 } \\ & \text { TSSOP-8 } \end{aligned}$ | $\begin{aligned} & \hline 185 \\ & 140 \end{aligned}$ | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| $\theta_{\text {Jc }}$ | Thermal Resistance (Junction-to-Case) | Standard Board | TSSOP-8 | 41 to 44 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| $\theta_{\mathrm{JA}}$ | Thermal Resistance (Junction-to-Ambient) | $\begin{aligned} & 0 \text { lfpm } \\ & 500 \text { lfpm } \end{aligned}$ | $\begin{aligned} & \text { DFN8 } \\ & \text { DFN8 } \end{aligned}$ | $\begin{gathered} \hline 129 \\ 84 \end{gathered}$ | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| $\mathrm{T}_{\text {sol }}$ | Wave Solder (Pb-Free) |  |  | 265 | ${ }^{\circ} \mathrm{C}$ |
| $\theta_{\text {Jc }}$ | Thermal Resistance (Junction-to-Case) | (Note 1) | DFN8 | 35 to 40 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. JEDEC standard multilayer board - 2S2P (2 signal, 2 power)

Table 4. PECL INPUT DC CHARACTERISTICS $\left(\mathrm{V}_{\mathrm{CC}}=3.3 \mathrm{~V}\right.$; GND $=0.0 \mathrm{~V}$ (Note 1))

| Symbol | Characteristic | $-40^{\circ} \mathrm{C}$ |  |  | $25^{\circ} \mathrm{C}$ |  |  | $85^{\circ} \mathrm{C}$ |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  | Min | Typ | Max | Min | Typ | Max | Min | Typ | Max |  |
| $\mathrm{V}_{\mathrm{IH}}$ | Input HIGH Voltage (Single-Ended) | 2075 |  | 2420 | 2075 |  | 2420 | 2075 |  | 2420 | mV |
| $\mathrm{V}_{\mathrm{IL}}$ | Input LOW Voltage (Single-Ended) | 1355 |  | 1675 | 1355 |  | 1675 | 1355 |  | 1675 | mV |
| $\mathrm{V}_{\mathrm{BB}}$ | Output Voltage Reference | 1775 | 1875 | 1975 | 1775 | 1875 | 1975 | 1775 | 1875 | 1975 | V |
| $\mathrm{V}_{\text {IHCMR }}$ | Input HIGH Voltage Common Mode Range (Differential) (Note 2) | 1.2 |  | 3.3 | 1.2 |  | 3.3 | 1.2 |  | 3.3 | V |
| $\mathrm{IIH}^{\text {H }}$ | Input HIGH Current |  |  | 150 |  |  | 150 |  |  | 150 | $\mu \mathrm{A}$ |
| IIL | Input LOW Current D D | $\begin{aligned} & -150 \\ & -150 \end{aligned}$ |  |  | $\begin{aligned} & -150 \\ & -150 \end{aligned}$ |  |  | $\begin{aligned} & -150 \\ & -150 \end{aligned}$ |  |  | $\mu \mathrm{A}$ |

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 Ifpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

1. Input parameters vary $1: 1$ with $\mathrm{V}_{\mathrm{CC}}$.
2. $\mathrm{V}_{\text {IHCMR }}$ min varies $1: 1$ with $G N D, \mathrm{~V}_{\text {IHCMR }}$ max varies $1: 1$ with $\mathrm{V}_{\mathrm{CC}}$. The $\mathrm{V}_{\text {IHCMR }}$ range is referenced to the most positive side of the differential input signal.

Table 5. TTL OUTPUT DC CHARACTERISTICS ( $\mathrm{V}_{\mathrm{CC}}=3.3 \mathrm{~V}$; GND $=0.0 \mathrm{~V} ; \mathrm{T}_{\mathrm{A}}=-40^{\circ} \mathrm{C}$ to $85^{\circ} \mathrm{C}$ )

| Symbol | Characteristic | Condition | Min | Typ | Max | Unit |
| :---: | :--- | :--- | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{OH}}$ | Output HIGH Voltage | $\mathrm{I}_{\mathrm{OH}}=-3.0 \mathrm{~mA}$ | 2.4 |  |  | V |
| $\mathrm{~V}_{\mathrm{OL}}$ | Output LOW Voltage | $\mathrm{I}_{\mathrm{OL}}=24 \mathrm{~mA}$ |  |  | 0.5 | V |
| $\mathrm{I}_{\mathrm{CCH}}$ | Power Supply Current |  | 10 | 25 | 35 | mA |
| $\mathrm{I}_{\mathrm{CCL}}$ | Power Supply Current |  | 15 | 34 | 40 | mA |
| $\mathrm{I}_{\mathrm{OS}}$ | Output Short Circuit Current |  | -50 |  | -150 | mA |

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm . Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

Table 6. AC CHARACTERISTICS $\left(\mathrm{V}_{\mathrm{CC}}=3.0 \mathrm{~V}\right.$ to 3.6 V ; GND $=0.0 \mathrm{~V}$ (Note 1))

| Symbol | Characteristic | $-40^{\circ} \mathrm{C}$ |  |  | $25^{\circ} \mathrm{C}$ |  |  | $85^{\circ} \mathrm{C}$ |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  | Min | Typ | Max | Min | Typ | Max | Min | Typ | Max |  |
| $f_{\text {max }}$ | Maximum Frequency (Figure 2) | 275 | 350 |  | 275 | 350 |  | 275 | 350 |  | MHz |
| $\begin{aligned} & \mathrm{t}_{\mathrm{pLLH}}, \\ & \mathrm{t}_{\mathrm{pH}}, \end{aligned}$ | Propagation Delay to Output Differential (Note 2) | $\begin{aligned} & 1.2 \\ & 1.2 \end{aligned}$ | $\begin{aligned} & 1.5 \\ & 1.5 \end{aligned}$ | $\begin{aligned} & 2.0 \\ & 1.8 \end{aligned}$ | $\begin{aligned} & 1.2 \\ & 1.2 \end{aligned}$ | $\begin{aligned} & 1.5 \\ & 1.5 \end{aligned}$ | $\begin{aligned} & 2.0 \\ & 1.8 \end{aligned}$ | $\begin{aligned} & 1.3 \\ & 1.2 \end{aligned}$ | $\begin{aligned} & 1.7 \\ & 1.5 \end{aligned}$ | $\begin{aligned} & 2.2 \\ & 1.8 \end{aligned}$ | ns |
| ${ }^{\text {tSK }}+$ tSK-tSKPP | Within Device Skew + + <br> Within Device Skew - - <br> Device-to-Device Skew (Note 3) |  | $\begin{gathered} 15 \\ 20 \\ 100 \end{gathered}$ | $\begin{gathered} 60 \\ 85 \\ 500 \end{gathered}$ |  | $\begin{gathered} 15 \\ 20 \\ 100 \end{gathered}$ | $\begin{aligned} & 60 \\ & 85 \\ & 500 \end{aligned}$ |  | $\begin{gathered} 20 \\ 30 \\ 100 \end{gathered}$ | $\begin{gathered} 85 \\ 85 \\ 500 \end{gathered}$ | ps |
| $\mathrm{t}_{\text {IITTER }}$ | $\begin{aligned} & \text { Random Clock Jitter (RMS) (Figure 2) } \\ & @ \leq 200 \mathrm{MHz} \\ & @>200 \mathrm{MHz} \end{aligned}$ |  | $\begin{gathered} 6 \\ 20 \end{gathered}$ | $\begin{gathered} 30 \\ 275 \end{gathered}$ |  | $\begin{gathered} 6 \\ 40 \end{gathered}$ | $\begin{gathered} 30 \\ 275 \end{gathered}$ |  | $\begin{gathered} 6 \\ 170 \end{gathered}$ | $\begin{gathered} 30 \\ 275 \end{gathered}$ | ps |
| $\mathrm{V}_{\mathrm{PP}}$ | Input Voltage Swing (Differential Configuration) | 150 | 800 | 1200 | 150 | 800 | 1200 | 150 | 800 | 1200 | mV |
| $\mathrm{t}_{\mathrm{r}}$ $\mathrm{t}_{\mathrm{f}}$ | Output Rise/Fall Times <br> ( $0.8 \mathrm{~V}-2.0 \mathrm{~V}$ ) | 330 | 600 | 950 | 330 | 600 | 950 | 330 | 650 | 950 | ps |

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm . Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

1. Measured with a $750 \mathrm{mV} 50 \%$ duty-cycle clock source. $R_{L}=500 \Omega$ to $G N D$ and $C_{L}=20 \mathrm{pF}$ to GND. Refer to Figure 3.
2. Reference $\left(\mathrm{V}_{\mathrm{CC}}=3.3 \mathrm{~V} \pm 5 \%\right.$; GND $=0 \mathrm{~V}$ )
3. Skews are measured between outputs under identical transitions.


Figure 2. Typical $\mathrm{V}_{\mathrm{OH}} /$ Jitter versus Frequency $\left(25^{\circ} \mathrm{C}\right)$


Figure 3. TTL Output Loading Used for Device Evaluation
Resource Reference of Application Notes
AN1405/D - ECL Clock Distribution Techniques
AN1406/D - Designing with PECL (ECL at +5.0 V)
AN1503/D - ECLinPS $^{m}$ I/O SPiCE Modeling Kit
AN1504/D - Metastability and the ECLinPS Family $^{\text {AN1568/D }}$ - Interfacing Between LVDS and ECL
AN1672/D - The ECL Translator Guide
AND8001/D - Odd Number Counters Design
AND8002/D - Marking and Date Codes
AND8020/D - Termination of ECL Logic Devices
AND8066/D - Interfacing with ECLinPS
AND8090/D - AC Characteristics of ECL Devices

DFN8 2x2, 0.5P
CASE 506AA-01
ISSUE E
DATE 22 JAN 2010

## SCALE 4:1



NOTES:
. Dimensioning and tolerancing per ASME Y14.5M, 1994
CONTROLLING DIMENSION: MILLIMETERS.
2. CIMENSION B APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20 MM FROM TERMINAL TIP.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

|  | MILLIMETERS |  |
| :---: | :---: | :---: |
| DIM | MIN | MAX |
| A | 0.80 | 1.00 |
| A1 | 0.00 | 0.05 |
| A3 | 0.20 REF |  |
| b | 0.20 | 10.30 |
| D | 2.00 BSC |  |
| D2 | 1.10 | 1.30 |
| E | 2.00 BS |  |
| E2 | 0.70 | 0.90 |
| e | 0.50 BSC |  |
| K | 0.30 REF |  |
| L | 0.25 | 0.35 |
| L1 | ---1 | 0.10 |

> GENERIC
> MARKING DIAGRAM*
> XX = Specific Device Code
> M = Date Code
> - = Pb-Free Device
*This information is generic. Please refer to device data sheet for actual part marking. $\mathrm{Pb}-\mathrm{Free}$ indicator, " G " or microdot " $\mathrm{\nabla}$ ", may or may not be present.

RECOMMENDED SOLDERING FOOTPRINT*

*For additional information on our Pb -Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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| ---: | :--- | :--- | :--- |
| DESCRIPTION: | DFN8, 2.0X2.0, 0.5MM PITCH | PAGE 1 OF 1 |

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SOIC-8 NB
CASE 751-07
ISSUE AK
SCALE 1:1
DATE 16 FEB 2011


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751-01 THRU 751-06 ARE OBSOLETE. NEW
7. 751-01 THRU 751-06 AR
STANDARD IS 751-07.

| DIM | MILLIMETERS |  | INCHES |  |
| :---: | :---: | :---: | :---: | :---: |
|  | MIN | MAX | MIN | MAX |
|  | 4.80 | 5.00 | 0.189 | 0.197 |
| B | 3.80 | 4.00 | 0.150 | 0.157 |
| C | 1.35 | 1.75 | 0.053 | 0.069 |
| D | 0.33 | 0.51 | 0.013 | 0.020 |
| G | 1.27 BSC |  | 0.050 BSC |  |
| H | 0.10 | 0.25 | 0.004 | 0.010 |
| J | 0.19 | 0.25 | 0.007 | 0.010 |
| K | 0.40 | 1.27 | 0.016 | 0.050 |
| M | 0 | $0^{\circ}$ | $8^{\circ}$ | 0 |
|  | $\circ$ | 8 |  |  |
| N | 0.25 | 0.50 | 0.010 | 0.020 |
| S | 5.80 | 6.20 | 0.228 | 0.244 |

## GENERIC

MARKING DIAGRAM*



XXXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week

- = Pb-Free Package
*This information is generic. Please refer to device data sheet for actual part marking. $\mathrm{Pb}-$ Free indicator, " $G$ " or microdot " r ", may or may not be present. Some products may not follow the Generic Marking.
*For additional information on our $\mathrm{Pb}-$ Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.


## STYLES ON PAGE 2

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| DESCRIPTION: | SOIC-8 NB | PAGE 1 OF 2 |

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SOIC-8 NB
CASE 751-07
ISSUE AK
DATE 16 FEB 2011

STYLE

| PIN 1. | EMITTER |
| ---: | :--- |
| 2. | COLLECTOR |
| 3. | COLLECTOR |
| 4. | EMITTER |
| 5. | EMITTER |
| 6. | BASE |
| 7. | BASE |
| 8. | EMITTER |
| STYLE 5: |  |
| PIN 1. | DRAIN |
| 2. | DRAIN |
| 3. | DRAIN |
| 4. | DRAIN |
| 5. | GATE |
| 6. | GATE |
| 7. | SOURCE |
| 8. | SOURCE |

STYLE 9:
PIN 1. EMITTER, COMMON
COLLECTOR, DIE \#1 COLLECTOR, DIE \#2 EMITTER, COMMON EMITTER, COMMON BASE, DIE \#2
BASE, DIE \#
8. EMITTER, COMMON

STYLE 13:
PIN 1. N.C.
2. SOURCE
3. SOURCE

GATE
DRAIN
DRAIN
DRAIN
8. DRAIN

STYLE 17:
PIN 1. VCC
V2OUT
V10UT
V10UT
TXE
RXE
VEE
7. GND
8. ACC

STYLE 21:
PIN 1. CATHODE 1
2. CATHODE 2
3. CATHODE 3

CATHODE 4
CATHODE 5
6. COMMON ANODE
7. COMMON ANODE
8. CATHODE 6

STYLE 25:
PIN 1. VIN
2. $N / C$

REXT
GND
IOUT
IOUT
IOUT
8. IOUT

## STYLE 29

PIN 1. BASE, DIE \#
EMITTER, \#1
BASE, \#2
. EMITTER, \#2
5. COLLECTOR, \#2
6. COLLECTOR, \#2
7. COLLECTOR, \#1
7. COLLECTOR, \#1

STYLE 2:
PIN 1. COLLECTOR,
2. COLLECTOR, \#1
3. COLLECTOR, \#2

COLLECTOR, \#2
BASE, \#2
. EMITTER, \#2
7. BASE, \#1
8. EMITTER, \#1

STYLE 6:
PIN 1. SOURCE
DRAIN
3. DRAIN
4. SOURCE

SOURCE
6. GATE
7. GATE
8. SOURCE

STYLE 10:
PIN 1. GROUND
2. BIAS 1
3. OUTPUT

GROUND
GROUND
BIAS 2
7. INPUT
8. GROUND

STYLE 14:
PIN 1. N-SOURCE
2. N-GATE

P-SOURCE
P-GATE
5. P-DRAIN
6. P-DRAIN
7. N -DRAIN
8. N -DRAIN

STYLE 18
PIN 1. ANODE
2. ANODE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. CATHODE
8. CATHODE

STYLE 22 :
PIN 1. I/O LINE
2. COMMON CATHODE/VCC
3. COMMON CATHODE/VCC
4. I/O LINE 3
5. COMMON ANODE/GND
6. I/O LINE 4
7. I/O LINE 5
8. COMMON ANODE/GND

STYLE 26:
PIN 1. GND
2. $\mathrm{dv} / \mathrm{dt}$
3. ENABLE
3. ENABLE
4. ILIMIT

SOURCE
SOURCE
SOURCE
8. VCC

STYLE 30:
PIN 1. DRAIN 1
2. DRAIN 1
3. GATE 2
4. SOURCE 2
5. SOURCE 1/DRAIN 2
. SOURCE 1/DRAIN 2
SOURCE 1/DRAIN 2
8. GATE 1

STYLE 3
STYLE
2. DRAIN, DIE
2. DRAIN, \#1
2. DRAIN, \#
3. DRAIN, \#2
4. DRAIN, \#2
5. GATE, \#2
7. GATE, \#1
8. SOURCE, \#1

## STYLE 7

PIN 1. INPUT
2. EXTERNAL BYPASS
3. THIRD STAGE SOURCE
4. GROUND
5. DRAIN
6. GATE 3
7. SECOND STAGE Vd
8. FIRST STAGE Vd

## STYLE 11:

PIN 1. SOURCE
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. DRAIN 2
7. DRAIN 1
8. DRAIN 1

## STYLE 15:

PIN 1. ANODE 1
2. ANODE 1
3. ANODE 1
4. ANODE 1
5. CATHODE, COMMON
6. CATHODE, COMMON
7. CATHODE, COMMON
8. CATHODE, COMMON

## STYLE 19:

PIN 1. SOURCE
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. MIRROR 2
7. DRAIN 1
8. MIRROR 1

## STYLE 23:

PIN 1. LINE 1 IN
2. COMMON ANODE/GND
3. COMMON ANODE/GND
4. LINE 2 IN
5. LINE 2 OUT
6. COMMON ANODE/GND
7. COMMON ANODE/GND
8. LINE 1 OUT

STYLE 27:
PIN 1. ILIMIT
2. OVLO
3. UVLO
4. INPUT+
5. INPUT+
5. SOURCE
6. SOURCE
7. SOURCE
8. DRAIN

STYLE 4:
PIN 1. ANODE
2. ANODE
3. ANODE
4. ANODE
5. ANODE
6. ANODE
8. COMMON CATHODE

## STYLE 8:

PIN 1. COLLECTOR, DIE \#1
2. BASE, \#1
3. BASE, \#2
4. COLLECTOR, \#2
5. COLLECTOR, \#2
6. EMITTER, \#2
7. EMITTER, \#1
8. COLLECTOR, \#1

## STYLE 12

PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

## STYLE 16:

PIN 1. EMITTER, DIE \#1
2. BASE, DIE \#1
3. EMITTER, DIE \#2
3. EMITTER, DIE
4. BASE, DIE \#2
4. BASE, DIE \#2
6. COLLECTOR, DIE \#2
7. COLLECTOR, DIE \#1
8. COLLECTOR, DIE \#1

## STYLE 20:

PIN 1. SOURCE (N)
2. GATE (N)
3. SOURCE (P)
4. GATE (P)
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 24
PIN 1. BASE
2. EMITTER
3. COLLECTOR/ANODE
4. COLLECTOR/ANODE
5. CATHODE
6. CATHODE
7. COLLECTOR/ANODE
8. COLLECTOR/ANODE

## STYLE 28:

PIN 1. SW_TO_GND
2. DASIC $\bar{O} F F$
3. DASIC_SW_DET
4. GND
5. V_MON
6. VBUULK
7. VBULK
8. VIN

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| :---: | :---: | :---: |
| DESCRIPTION: | SOIC-8 NB | PAGE 2 OF 2 |

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TSSOP 8

## CASE 948R-02

ISSUE A
DATE 04/07/2000

## SCALE 2:1


notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PROTRUSI
PER SIDE
5. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY
6. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-

|  | MILLIMETERS |  | INCHES |  |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| DIM | MIN | MAX | MIN | MAX |  |  |
| A | 2.90 | 3.10 | 0.114 | 0.122 |  |  |
| B | 2.90 | 3.10 | 0.114 | 0.122 |  |  |
| C | 0.80 | 1.10 | 0.031 | 0.043 |  |  |
| D | 0.05 | 0.15 | 0.002 | 0.006 |  |  |
| F | 0.40 | 0.70 | 0.016 | 0.028 |  |  |
| G | 0.65 BSC |  | 0.026 BSC |  |  |  |
| K | 0.25 |  | 0.40 | 0.010 |  | 0.016 |
| L | 4.90 BSC |  | 0.193 BSC |  |  |  |
| M | $0^{\circ}$ |  | $6^{\circ}$ | $0^{\circ}$ |  | $6^{\circ}$ |


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| ---: | :--- | :--- | :--- |
| DESCRIPTION: | TSSOP 8 | PAGE 1 OF 1 |

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